



FTP18N06N

N-Channel Trench MOSFET

Pb Lead Free Package and Finish

Applications:

- Automotive
- DC Motor Control
- Class D Amplifier

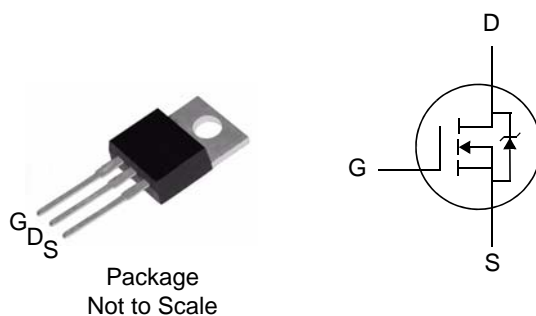
V_{DSS}	$R_{DS(ON)}$ (Max.)	I_D
60V	18 m Ω	55A

Features:

- RoHS Compliant
- Low ON Resistance
- Low Gate Charge
- Peak Current vs Pulse Width Curve
- Inductive Switching Curves

Ordering Information

PART NUMBER	PACKAGE	BRAND
FTP18N06N	TO-220	FTP18N06N



Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Maximum	Units
V_{DSS}	Drain-to-Source Voltage (NOTE *1)	60	V
I_D	Continuous Drain Current	55	A
$I_{D@ 100^\circ\text{C}}$	Continuous Drain Current	Figure 3	
I_{DM}	Pulsed Drain Current, $V_{GS}@ 10\text{V}$ (NOTE *2)	Figure 6	
P_D	Power Dissipation	130	W
	Derating Factor above 25°C	0.87	W/ $^\circ\text{C}$
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy $L=10\text{ mH}$, $I_D=8.0\text{ Amps}$	320	mJ
I_{AS}	Pulsed Avalanche Rating	Figure 8	
dv/dt	Peak Diode Recovery dv/dt (NOTE *3)	3.0	V/ns
T_L T_{PKG}	Maximum Temperature for Soldering Leads at 0.063in (1.6mm) from Case for 10 seconds	300	$^\circ\text{C}$
	Package Body for 10 seconds	260	
T_J and T_{STG}	Operating Junction and Storage Temperature Range	-55 to 175	

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" Table may cause permanent damage to the device.

Thermal Resistance

Symbol	Parameter	Maximum	Units	Test Conditions
$R_{\theta JC}$	Junction-to-Case	1.15	$^\circ\text{C}/\text{W}$	Drain Lead soldered to water cooled heatsink, P_D adjusted for a peak junction temperature of $+175^\circ\text{C}$.
$R_{\theta JA}$	Junction-to-Ambient	62		1 cubic foot chamber, free air.

OFF Characteristics $T_J=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	60	--	--	V	$V_{GS}=0V, I_D=250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temperature Coefficient, Figure 11.	--	0.71	--	V/ $^\circ\text{C}$	Reference to 25°C , $I_D=250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	--	--	25	μA	$V_{DS}=60V, V_{GS}=0V$
		--	--	250		$V_{DS}=48V, V_{GS}=0V$ $T_J=150^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	--	--	100	nA	$V_{GS}=+20V$
	Gate-to-Source Reverse Leakage	--	--	-100		$V_{GS}=-20V$

ON Characteristics $T_J=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance Figure 9 and 10.	--	16	18	$m\Omega$	$V_{GS}=10V, I_D=33A$ (NOTE *4)
$V_{GS(TH)}$	Gate Threshold Voltage, Figure 12.	2.0	--	4.0	V	$V_{DS}=V_{GS}, I_D=250\mu A$
gfs	Forward Transconductance	--	65	--	S	$V_{DS}=30V, I_D=55A$ (NOTE *4)

Dynamic Characteristics Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
C_{iss}	Input Capacitance	--	2077	--	pF	$V_{GS}=0V$ $V_{DS}=25V$ $f=1.0MHz$ Figure 14
C_{oss}	Output Capacitance	--	222	--		
C_{riss}	Reverse Transfer Capacitance	--	115	--		
Q_g	Total Gate Charge	--	33.6	--	nC	$V_{DD}=30V$ $I_D=55A$ Figure 15
Q_{gs}	Gate-to-Source Charge	--	9.1	--		
Q_{gd}	Gate-to-Drain ("Miller") Charge	--	7.6	--		

Resistive Switching Characteristics Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$t_{d(ON)}$	Turn-on Delay Time	--	24	--	ns	$V_{DD}=30V$ $I_D=27.5A$ $V_{GS}=10V$ $R_G=9.1\Omega$
t_{rise}	Rise Time	--	37	--		
$t_{d(OFF)}$	Turn-Off Delay Time	--	71	--		
t_{fall}	Fall Time	--	65	--		

Source-Drain Diode Characteristics $T_C=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	--	--	55	A	Integral pn-diode in MOSFET
I_{SM}	Maximum Pulsed Current (Body Diode)	--	--	220	A	
V_{SD}	Diode Forward Voltage	--	--	1.5	V	$I_S=55\text{A}$, $V_{GS}=0\text{V}$
t_{rr}	Reverse Recovery Time	--	62	92.5	ns	$V_{GS}=0\text{V}$, $V_{DD}=-30\text{V}$ $I_F=55\text{A}$, $di/dt=100\text{A}/\mu\text{s}$
Q_{rr}	Reverse Recovery Charge	--	109	163.5	nC	

Notes:

*1. $T_J = +25^\circ\text{C}$ to $+175^\circ\text{C}$.

*2. Repetitive rating; pulse width limited by maximum junction temperature.

*3. $I_{SD} = 55\text{A}$ $di/dt \leq 100\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, $T_J = +175^\circ\text{C}$.

*4. Pulse width $\leq 380\mu\text{s}$; duty cycle $\leq 2\%$.

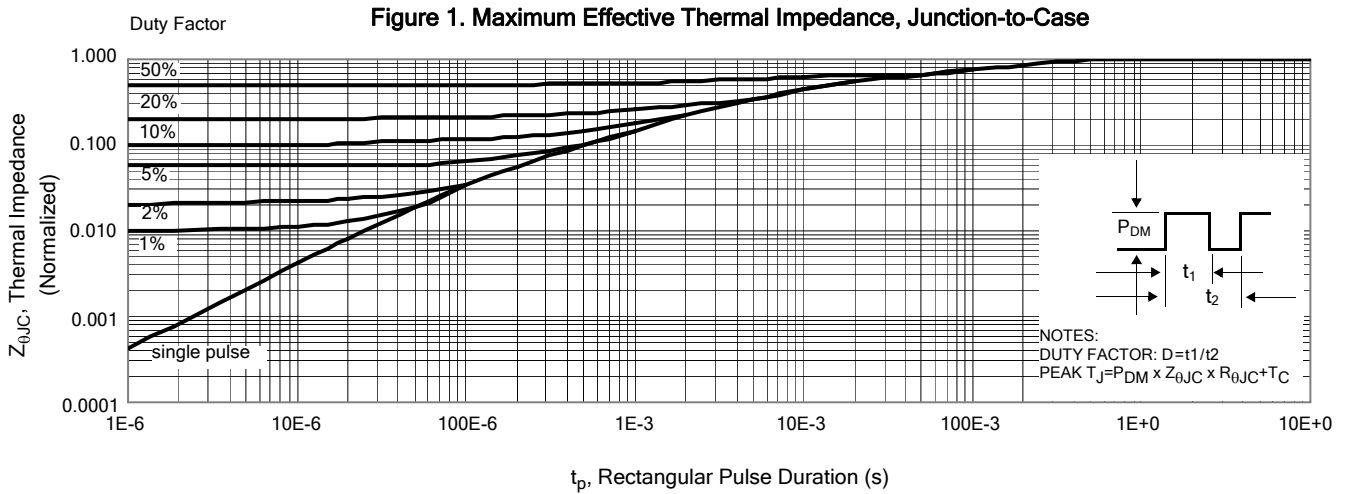


Figure 2. Maximum Power Dissipation vs Case Temperature

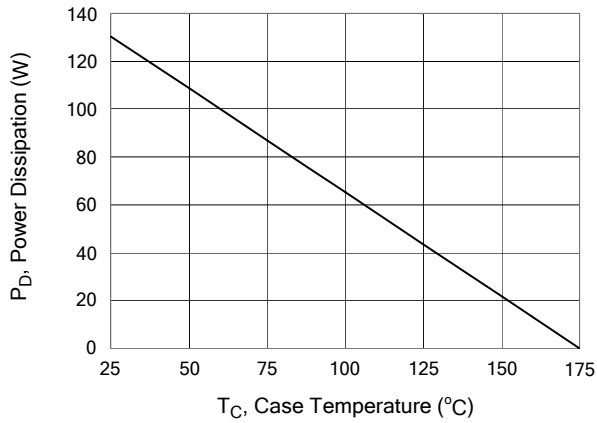


Figure 3. Maximum Continuous Drain Current vs Case Temperature

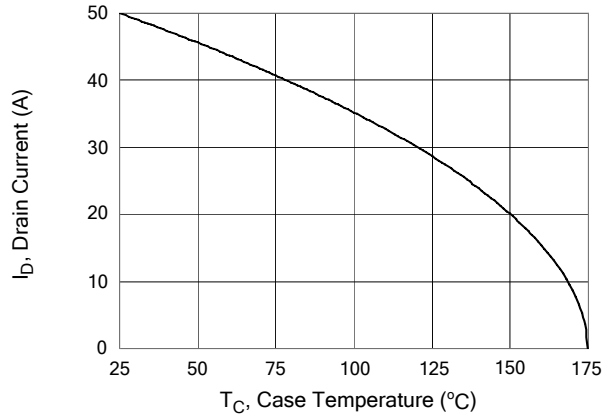


Figure 4. Typical Output Characteristics

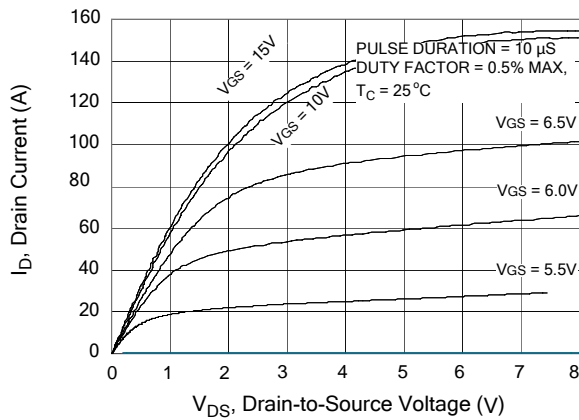


Figure 5. Typical Drain-to-Source ON Resistance vs Gate Voltage and Drain Current

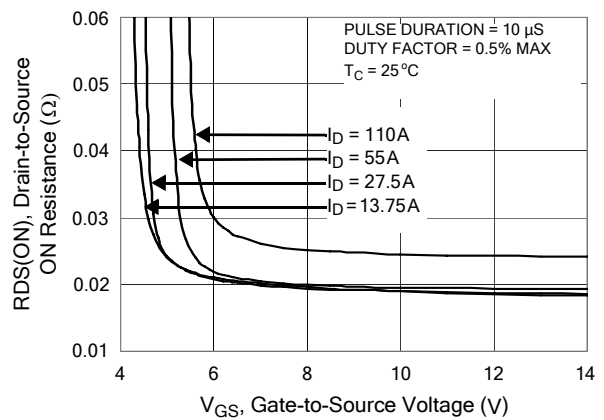


Figure 6. Maximum Peak Current Capability

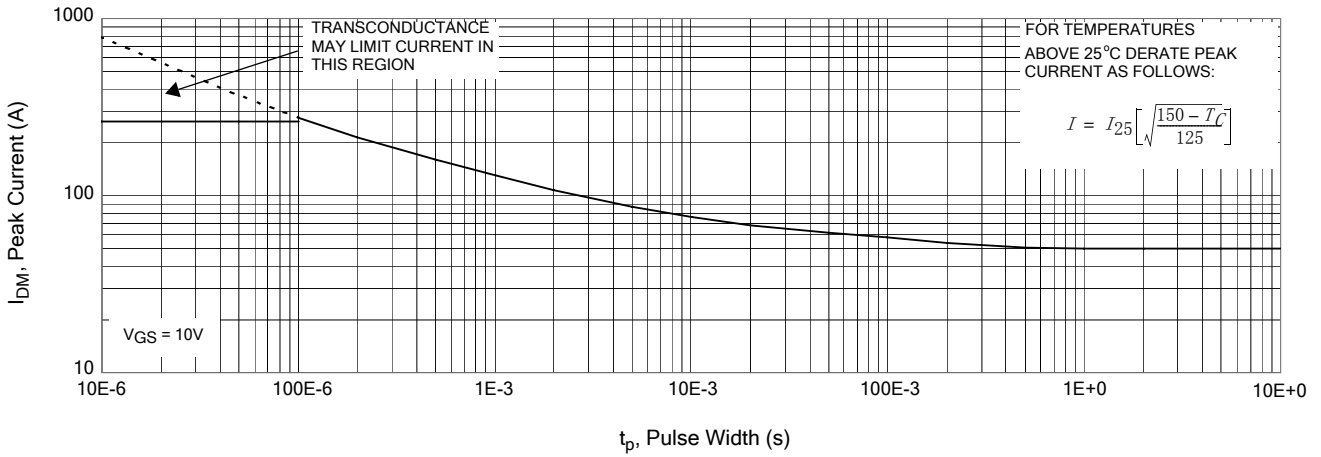


Figure 7. Typical Transfer Characteristics

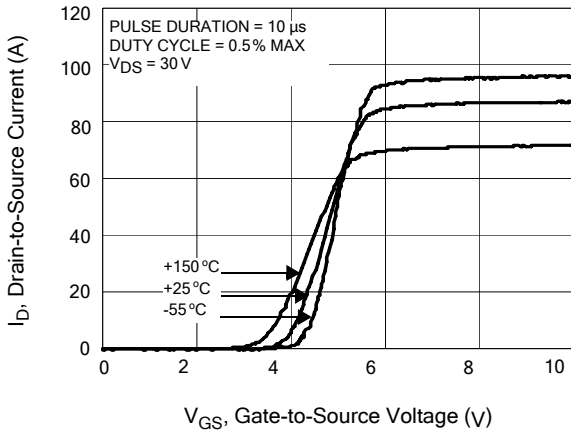


Figure 8. Unclamped Inductive Switching Capability

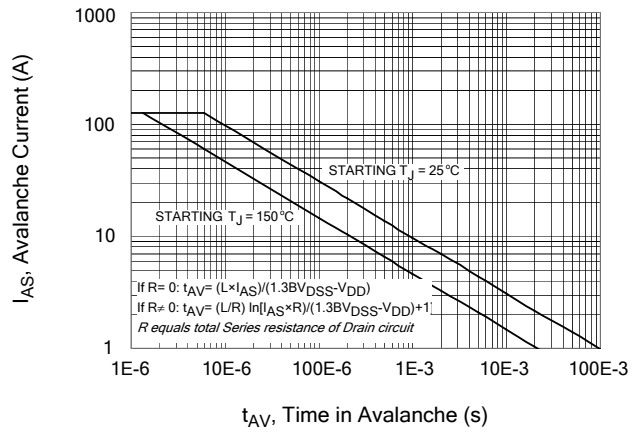


Figure 9. Typical Drain-to-Source ON Resistance vs Drain Current

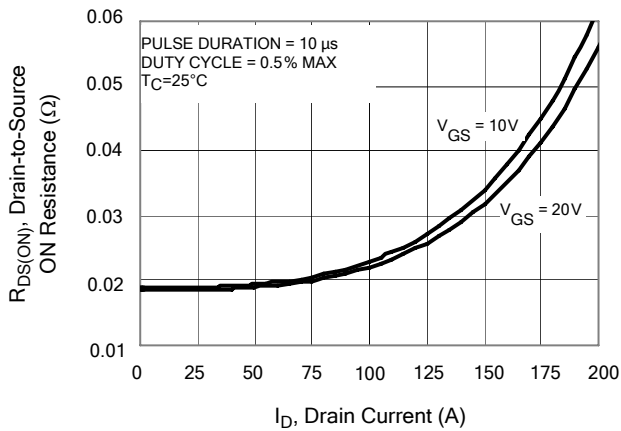


Figure 10. Typical Drain-to-Source ON Resistance vs Junction Temperature

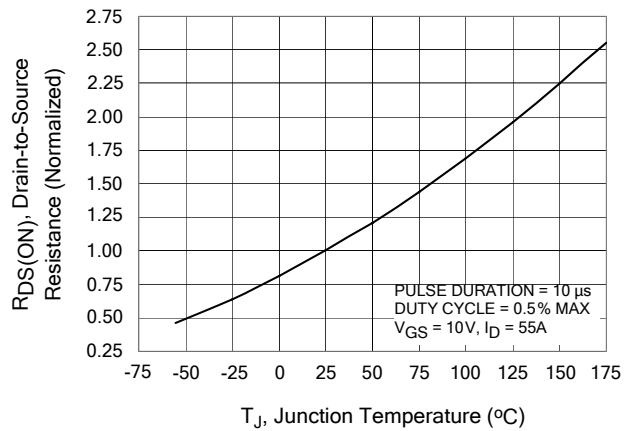


Figure 11. Typical Breakdown Voltage vs Junction Temperature

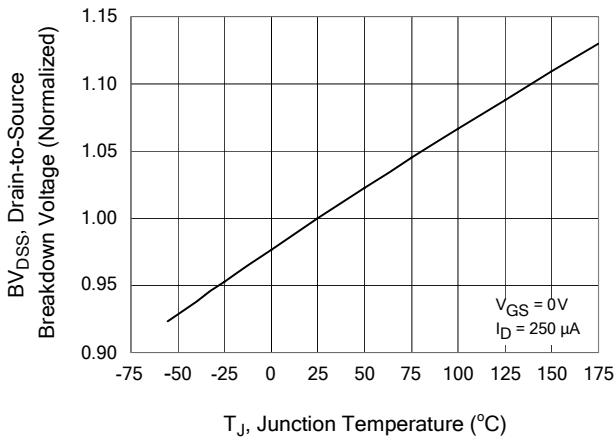


Figure 12. Typical Threshold Voltage vs Junction Temperature

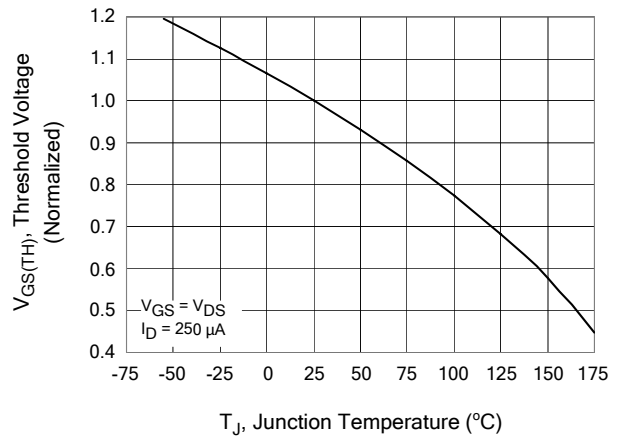


Figure 13. Maximum Forward Bias Safe Operating Area

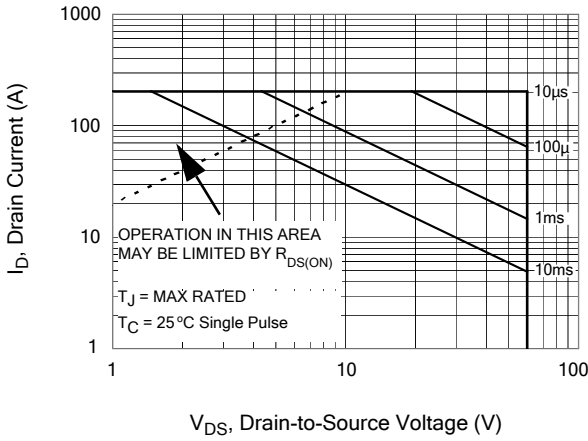


Figure 14. Typical Capacitance vs Drain-to-Source Voltage

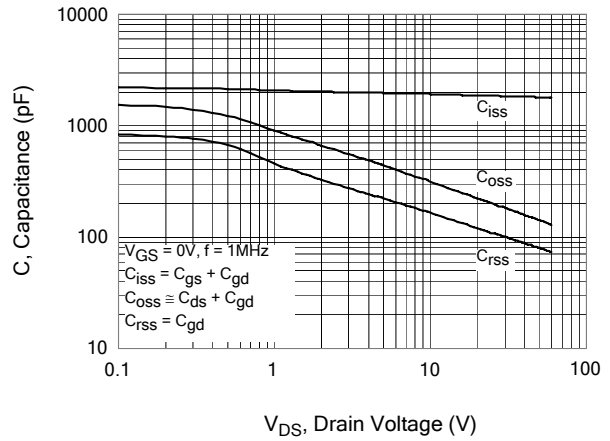


Figure 15. Typical Gate Charge vs Gate-to-Source Voltage

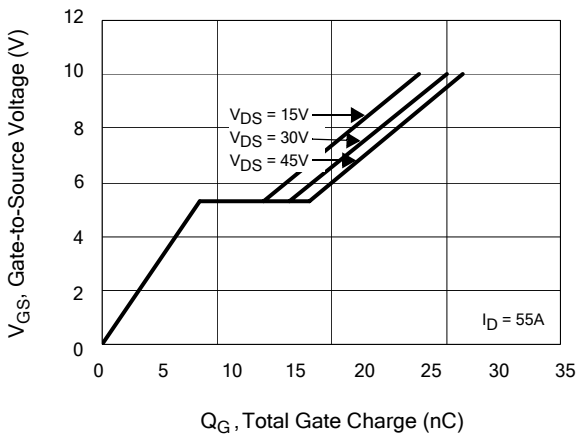
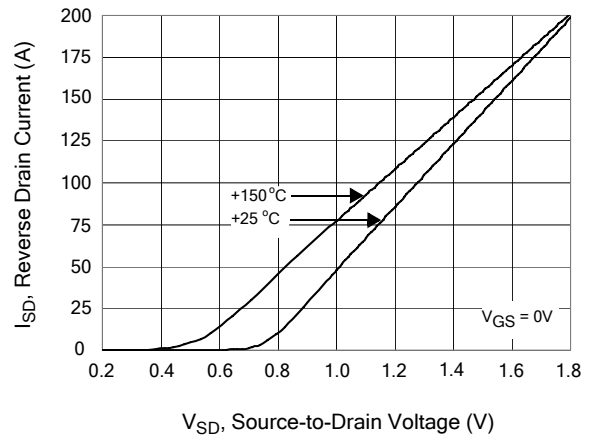


Figure 16. Typical Body Diode Transfer Characteristics



Test Circuits and Waveforms

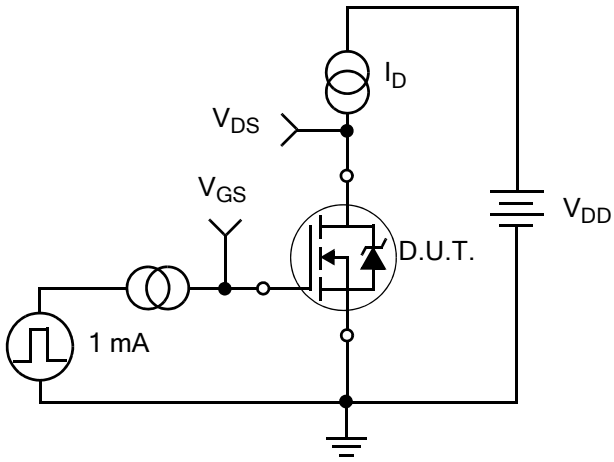


Figure 17. Gate Charge Test Circuit

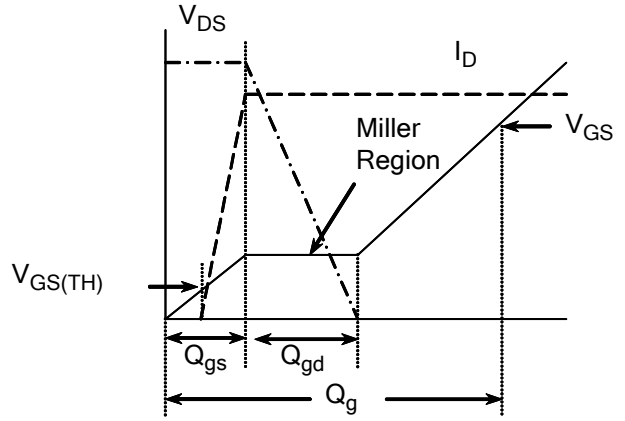


Figure 18. Gate Charge Waveform

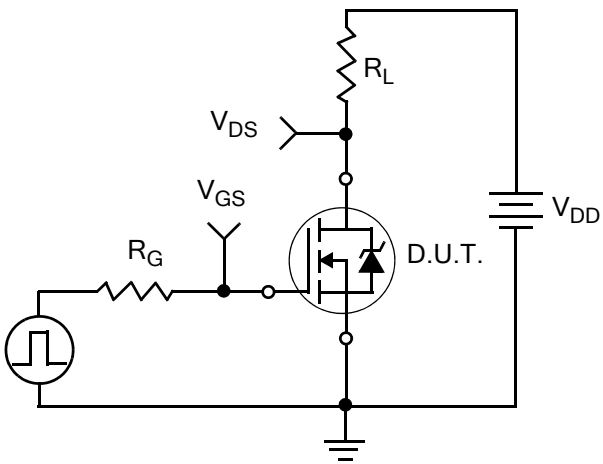


Figure 19. Resistive Switching Test Circuit

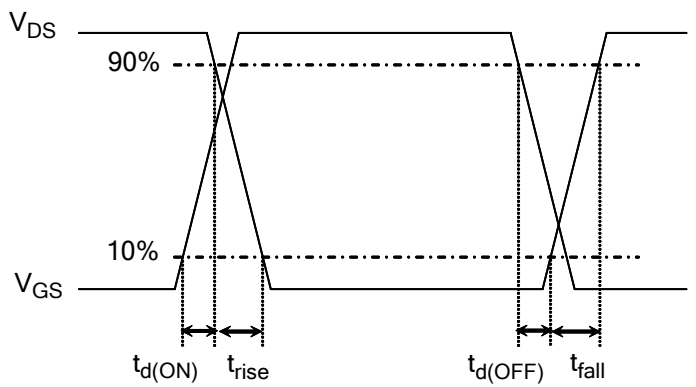


Figure 20. Resistive Switching Waveforms

Test Circuits and Waveforms

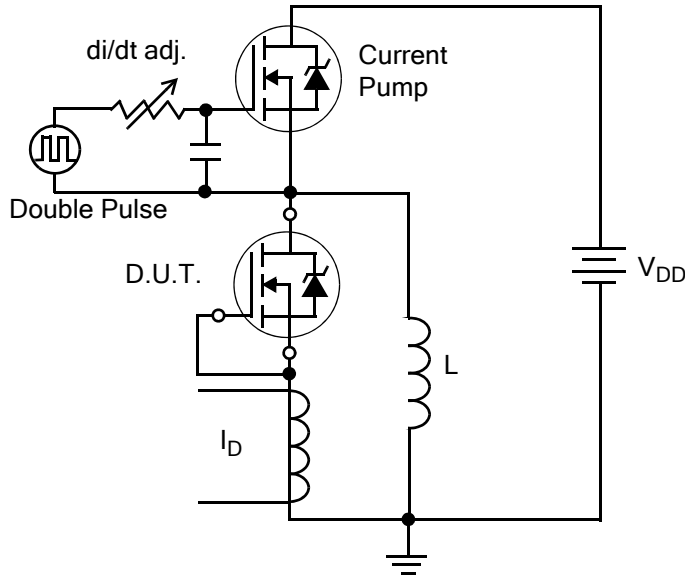


Figure 21. Diode Reverse Recovery Test Circuit

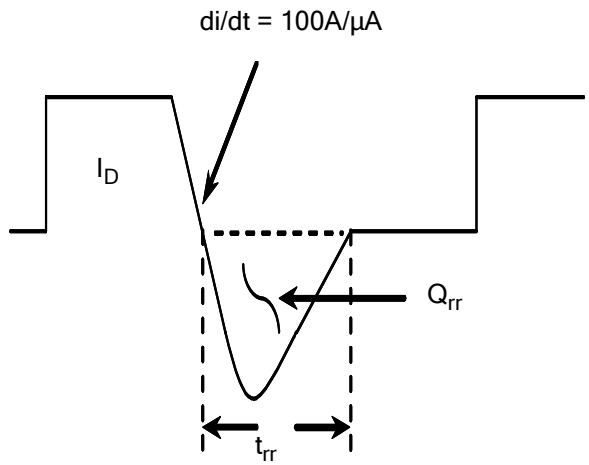


Figure 22. Diode Reverse Recovery Waveform

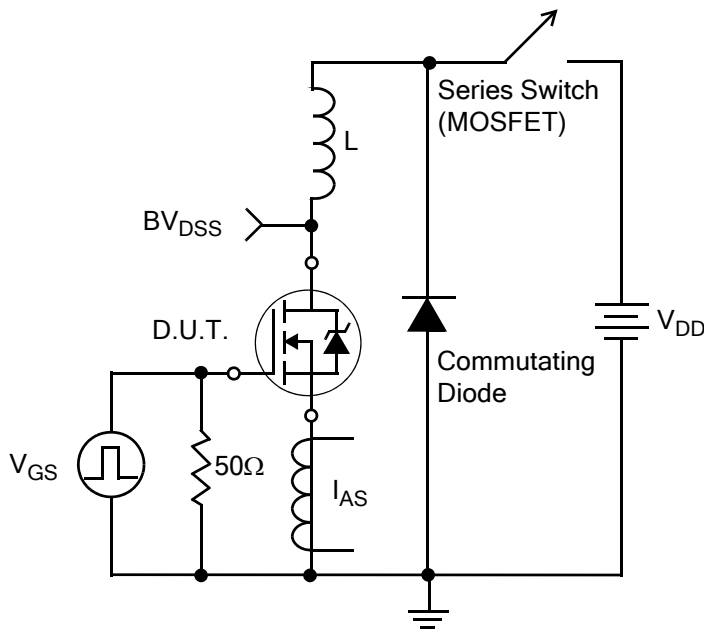


Figure 23. Unclamped Inductive Switching Test Circuit

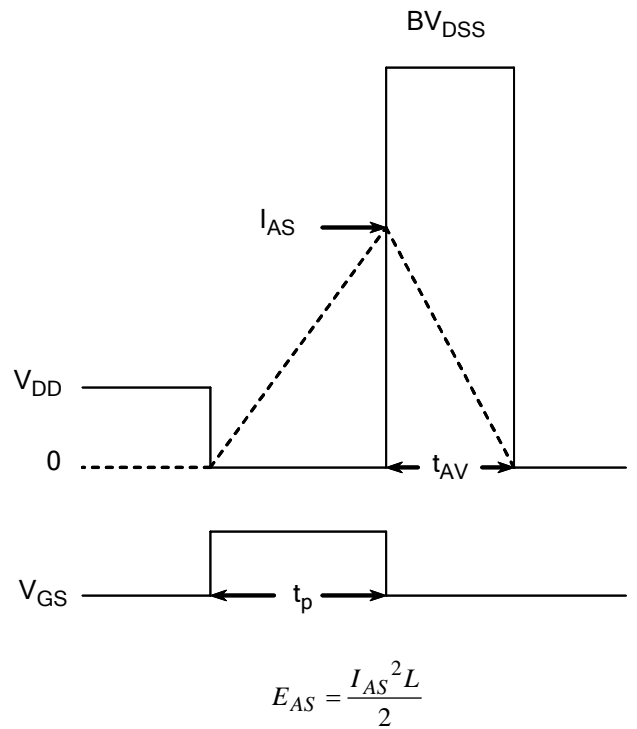


Figure 24. Unclamped Inductive Switching Waveforms

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